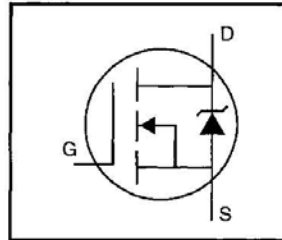


# IRFI644GPbF

## HEXFET® Power MOSFET

- Isolated Package
- High Voltage Isolation= 2.5KV RMS ⑤
- Sink to Lead Creepage Dist.= 4.8mm
- Dynamic dv/dt Rating
- Low Thermal Resistance
- Lead-Free

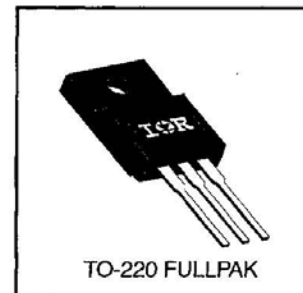


$V_{DSS} = 250V$
$R_{DS(on)} = 0.28\Omega$
$I_D = 7.9A$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	7.9	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	5.0	
$I_{DM}$	Pulsed Drain Current ①	32	
$P_D @ T_C = 25^\circ C$	Power Dissipation	40	W
	Linear Derating Factor	0.32	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	600	mJ
$I_{AR}$	Avalanche Current ①	7.9	A
$E_{AR}$	Repetitive Avalanche Energy ①	4.0	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.8	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1 N•m)	

### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	3.1	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	—	65	

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	250	—	—	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.34	—	V/°C	Reference to 25°C, I <sub>D</sub> =1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.28	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =4.7A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
g <sub>fs</sub>	Forward Transconductance	6.0	—	—	S	V <sub>DS</sub> =50V, I <sub>D</sub> =4.7A ④
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> =250V, V <sub>GS</sub> =0V
		—	—	250		V <sub>DS</sub> =200V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> =20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> =-20V
Q <sub>g</sub>	Total Gate Charge	—	—	68	nC	I <sub>D</sub> =7.9A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	11		V <sub>DS</sub> =200V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	35		V <sub>GS</sub> =10V See Fig. 6 and 13 ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	11	—	ns	V <sub>DD</sub> =125V
t <sub>r</sub>	Rise Time	—	24	—		I <sub>D</sub> =7.9A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	53	—		R <sub>G</sub> =9.1Ω
t <sub>f</sub>	Fall Time	—	24	—		R <sub>D</sub> =16Ω See Figure 10 ④
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	1300	—	pF	V <sub>GS</sub> =0V
C <sub>oss</sub>	Output Capacitance	—	330	—		V <sub>DS</sub> =25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	85	—		f=1.0MHz See Figure 5
C	Drain to Sink Capacitance	—	12	—		f=1.0MHz

## Source-Drain Ratings and Characteristics

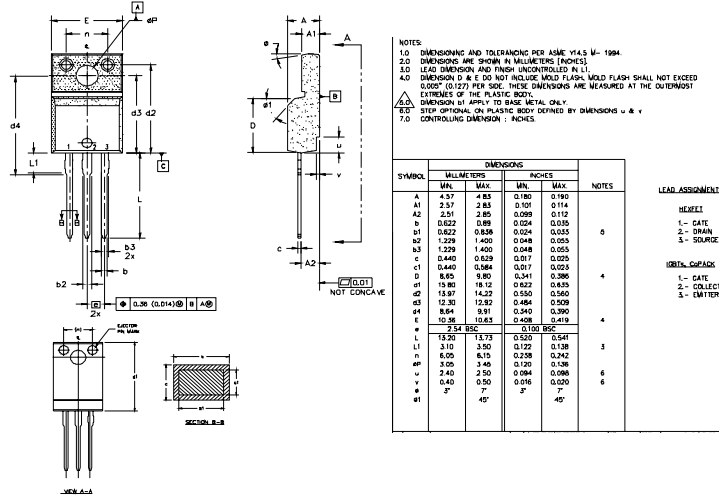
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	7.9	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	32		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.8	V	T <sub>J</sub> =25°C, I <sub>S</sub> =7.9A, V <sub>GS</sub> =0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	250	500	ns	T <sub>J</sub> =25°C, I <sub>F</sub> =7.9A
Q <sub>rr</sub>	Reverse Recovery Charge	—	2.3	4.6	μC	di/dt=100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ② V<sub>DD</sub>=50V, starting T<sub>J</sub>=25°C, L=15mH, R<sub>G</sub>=25Ω, I<sub>AS</sub>=7.9A (See Figure 12)
- ③ I<sub>SD</sub>≤7.9A, di/dt≤150A/μs, V<sub>DD</sub>≤V<sub>(BR)DSS</sub>, T<sub>J</sub>≤150°C
- ④ Pulse width ≤ 300 μs; duty cycle ≤2%
- ⑤ t=60s, f=60Hz

## TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



## TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G  
WITH ASSEMBLY  
LOT CODE 3432  
ASSEMBLED ON WW 24 1999  
IN THE ASSEMBLY LINE "K"

**Note:** "P" in assembly line position indicates "Lead-Free"

